

surface by a high intensity plasma conditioning treatment after the part having been installed in the processing chamber, the conditioning treatment comprising treating the exposed surface with a high density plasma while seasoning the processing chamber;

(b) processing the at least one substrate by supplying process gas to the processing chamber; and

(c) removing the at least one substrate from the processing chamber.

35. (New) The method according to Claim 1, further comprising:

- a) installing the ceramic part in the processing chamber;
- b) after a), treating the surface of the ceramic part by the high intensity plasma conditioning treatment in the processing chamber; and
- c) after b), processing production wafers in the processing chamber.

36. (New) The method according to Claim 15, further comprising:

- a) installing the ceramic part in a plasma reactor;
- b) after a), treating the surface of the ceramic part with the high intensity plasma in the plasma reactor; and
- c) after b), processing production wafers in the plasma reactor.